

Product Overview

The NSIP3266E H-bridge transformer driver provides a simple solution for designing isolated power supplies. The device drives the primary coil of the transformer with a voltage range from 6.5V to 26V. The transformer's secondary-to-primary turn ratio defines the output voltage, allowing selection of virtually any isolated output voltage.

The NSIP3266E features adjustable switching frequency from 100 kHz to 1MHz with an external resistor, which provides the flexibility to optimize either efficiency or external component size.

A $\overline{\text{FAULT}}$ output is asserted when the device detects an overtemperature or overcurrent condition. In addition, the device features a low-power mode to reduce the overall supply current to 0.7mA (typ) when the driver is disabled.

The NSIP3266E is available in HMSOP8 package with operating temperature range from -40°C to 125°C.

Key Features

- Wide supply voltage range: 6.5 to 26V
With input 12V, the maximum output power is 5W
- Ability to handle negative swing of (-10V) at EN pin
- Fault Detection and Indication
- Adjustable Frequency: 100 kHz to 1MHz
- Over-Temperature Protection
- Over-Current Protection
- Low supply current when disable
- Undervoltage Lockout for input voltage
- Operating temperature range: -40°C to 125°
- RoHS & REACH Compliance

Applications

- GaN, IGBT and SiC gate transformer driver bias supply
- UPS and solar inverters
- Industrial motors, elevators and escalators

Device Information

Part Number	Package	Body Size
NSIP3266E-DHMSR	HMSOP8	3.0 mm × 3.0 mm

Block Diagram

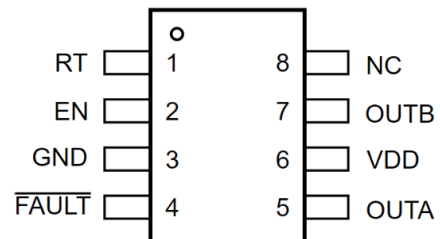


Figure 1. NSIP3266E

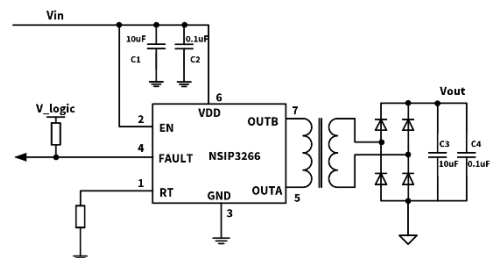


Figure 2. Simplified Schemati

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1. Pin Configuration and Functions

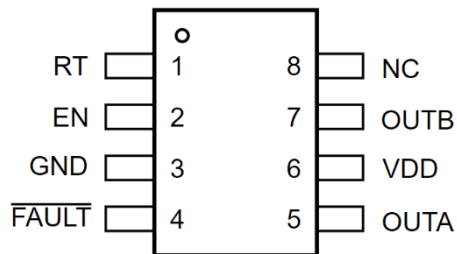


Figure 1.1 NSIP3266E Pin Configuration

Table 1.1 NSIP3266E Pin Description

NSIP3266E PIN NO.	SYMBOL	FUNCTION
1	RT	Frequency Setting Configure switching frequency (100 kHz–1 MHz) via external resistor between RT and GND. Defaults to 200 kHz if left floating.
2	EN	Enable Control Enable: Tie to VDD or floating; Disable: Connect to GND. Disables all internal circuits.
3	GND	Ground Common reference for power and signals.
4	$\overline{\text{FAULT}}$	Open-Drain $\overline{\text{FAULT}}$ Indicator Active Low: Asserted during OCP (overcurrent) or OTP (overtemperature); High-Z: Normal operation. Requires external pull-up resistor (e.g., 10k Ω) to monitor status.
5	OUTA	Transformer Drive Output A H-bridge driver output for primary-side switching.
6	VDD	Supply Voltage Input voltage (6.5V–26V).
7	OUTB	Transformer Drive Output B H-bridge driver output for primary-side switching.
8	NC	No Connection Leave unconnected.
EP	GND	Thermal Pad Internally connected to GND. Solder to PCB ground plane with multiple vias for heat dissipation.

2. Absolute Maximum Ratings

Parameters	Symbol	Min	Max	Unit	Comments
Supply Voltage	V _{DD}	-0.3	30	V	
Output Voltage	V _{OUTA} , V _{OUTB}	-0.3	V _{DD} +0.3	V	
		-2.0	V _{DD} +2.0	V	Pulse<200ns
V _{OUTA} , V _{OUTB} I _{PK} Current	I _{out(max)}		0.8	A	
Enable Pins Voltage	EN	-10	V _{DD}	V	
FAULT to GND	FAULT	-0.3	6	V	
RT to GND	RT	-0.3	6	V	
Operating Junction Temperature	T _J	-40	150	°C	
Storage Temperature	T _{STG}	-55	150	°C	

3. ESD Ratings

Parameters	Ratings	Value	Unit
Electrostatic discharge	Human body model (HBM), per AEC-Q100-002-RevD ● All pins	±2.0	kV
	Charged device model (CDM), per AEC-Q100-011-RevB ● All pins	±2.0	kV

4. Recommended Operating Conditions

Parameters	Symbol	Min	Max	Unit
Supply Voltage	V _{DD}	6.5	26	V
V _{OUTA} , V _{OUTB} Continuous Current (RMS)	I _{out(rms)}		0.5	A
Enable Pin Voltage	V _{EN}	-6	V _{DD}	V
Operating Ambient Temperature	T _A	-40	125	°C

5. Thermal Information

Parameters	Symbol	HMSOP8	Unit
IC Junction-to-Air Thermal Resistance ⁽¹⁾	θ _{JA}	58.5	°C/W
Junction-to-Board Thermal Resistance ⁽¹⁾	θ _{JB}	28.2	°C/W
Junction-to-Case (Top) Thermal Resistance ⁽¹⁾	θ _{JC(top)}	57.6	°C/W
Junction-to-Top Characterization Parameter ⁽¹⁾	Ψ _{JT}	5.4	°C/W
Junction-to-Board Characterization Parameter ⁽¹⁾	Ψ _{JB}	27.9	°C/W

(1) The thermal resistances (θ) are based on four layers 2s2p PCB JEDEC JESD 51-7.

(2) The characterization parameters (Ψ) are based on the EVM described in the Layout section.

6. Electrical Characteristics

Over full range of recommended operating conditions, unless otherwise noted. All typical values are at $T_A = 25^\circ\text{C}$, $V_{DD} = 12\text{ V}$.

Parameters	Symbol	Min	Typ	Max	Unit	Comments
Bias Currents						
Average supply current	I_{DD}	1.4	1.9	2.4	mA	$V_{DD} = 12\text{V}$, $F_{sw} = 200\text{kHz}$, $EN = V_{DD}$
Disable supply current	I_{DIS}	0.6	0.9	1.2	mA	$V_{DD} = 12\text{V}$, $EN = \text{GND}$
Over current protection threshold ⁽¹⁾	$I_{threshold}$	1.5	2.6	3.2	A	
Deglintch time of OUTA or OUTB short circuit protection ⁽²⁾	T_{SCP}		500		ns	
Under Voltage Lockout (UVLO)						
V_{DD} turn-on threshold	$V_{DD\ ON}$		4.7	4.9	V	V_{DD} rising until device activation
V_{DD} turn-off threshold	$V_{DD\ OFF}$	4.1	4.4		V	V_{DD} falling until device shutdown
V_{DD} hysteresis	$V_{DD\ HYS}$		0.3		V	V_{DD} voltage difference between turn-on and turn-off thresholds
Enable Characteristics						
Enable signal high transition	V_{EN_H}		2.1	2.6	V	EN rising until device activation
Enable signal low transition	V_{EN_L}	1.0	1.3		V	EN falling until device shutdown
Enable signal hysteresis	$V_{EN\ HYS}$		0.8		V	EN voltage difference between turn-on and turn-off thresholds
Output Characteristics						
Output pull-up resistance	R_{OH}		1.26	2.0	Ω	$I_{OUT} = -100\text{mA}$, $V_{DD} = 12\text{V}$
Output pull-down resistance	R_{OL}		0.65	1.5	Ω	$I_{OUT} = 100\text{mA}$, $V_{DD} = 12\text{V}$
Max soft start time ⁽²⁾	SST_{max}		40		ms	Current limiting time during soft start
Current limit ⁽²⁾	I_{limit}		550		mA	Current limit value during soft start
OUTA, OUTB leakage current ⁽²⁾	I_{LKG}		0.02		μA	$EN = \text{GND}$, OUTA/OUTB is GND or V_{DD}
FAULT Open Drain Output⁽²⁾						
Output low voltage	V_{OL}			0.5	V	Output is asserted, $I_{OL} = 5\text{mA}$
Leakage current at output high level	I_{LKG_FAULT}		0.4	1	μA	$\overline{\text{FAULT}}$ is not asserted, $V_{FAULT} = 6\text{V}$
Thermal Shut Down⁽¹⁾						
T_{SD} turn on temperature	T_{SD+}		175	181	$^\circ\text{C}$	T_{SD} rising until device shutdown
T_{SD} turn off temperature	T_{SD-}	135	150		$^\circ\text{C}$	T_{SD} falling until device activation
T_{SD} hysteresis	$T_{SD\ HYS}$		25		$^\circ\text{C}$	T_{SD} thermal difference between turn-on and turn-off thresholds

(1) Not test covered, Guaranteed by characterization.

(2) Not test covered, Guaranteed by design.

7. Switching Characteristics

Over full range of recommended operating conditions, unless otherwise noted. All typical values are at $T_A = 25^\circ\text{C}$, $V_{DD} = 12\text{ V}$.

Parameters	Symbol	Min	Typ	Max	Unit	Comments
Initial switching frequency	F_{sw0}	160	200	230	kHz	RT pin floating
Adjustable switching frequency ⁽²⁾	F_{sw}	100		1000	kHz	
Switching frequency at $R_T = 39\text{k}\Omega$	$F_{sw\ 39\text{k}\Omega}$	370	417	455	kHz	$R_T = 39\text{k}\Omega$
Rise time ⁽²⁾	T_R		30		ns	OUTA/OUTB = 20% to 80% of V_{DD} , $R_L = 50\Omega$, $C_L = 50\text{pF}$, $V_{DD} = 12\text{V}$, showing in Figure 9.1
Fall time ⁽²⁾	T_F		30		ns	OUTA/OUTB = 80% to 20% of V_{DD} , $R_L = 50\Omega$, $C_L = 50\text{pF}$, $V_{DD} = 12\text{V}$, showing in Figure 9.1
Dead time ⁽¹⁾	DT		5		ns	Connect a $20\ \Omega$ resistor in series between OUTA and OUTB., showing in Figure 9.2
EN Blanking Time ⁽¹⁾	T_{BLANK}		2.3	3	μs	
Spread Spectrum Clocking⁽²⁾						
Spread spectrum clocking range	Δf_c		$\pm 7\%$			
Spread spectrum modulation frequency	fm		3.125		kHz	

(1) Not test covered, Guaranteed by characterization.

(2) Not test covered, Guaranteed by design.

8. Typical Characteristics

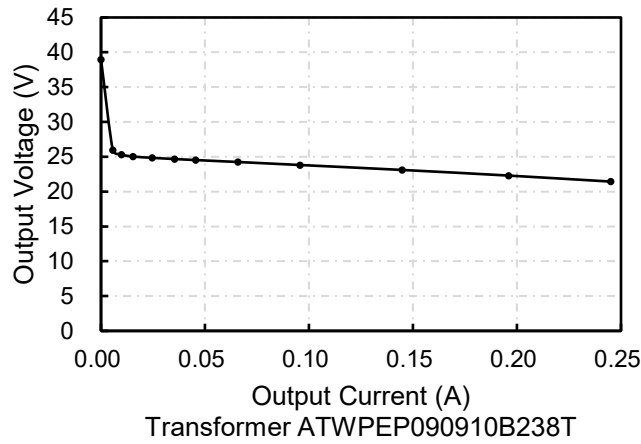


Figure 8.1 Output Voltage vs Load Current at VDD = 12V

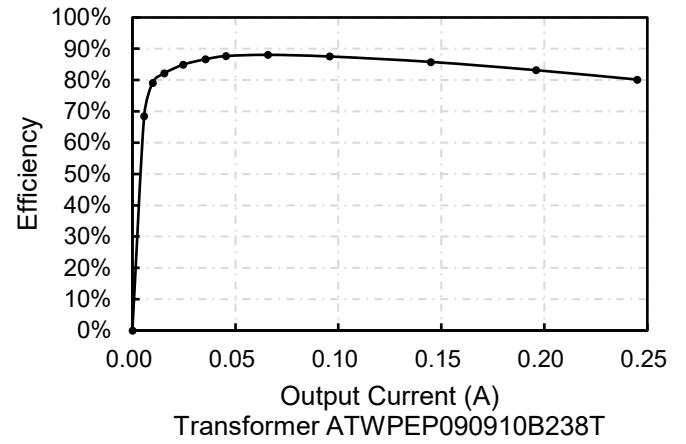


Figure 8.2 Efficiency vs Load Current at VDD = 12V

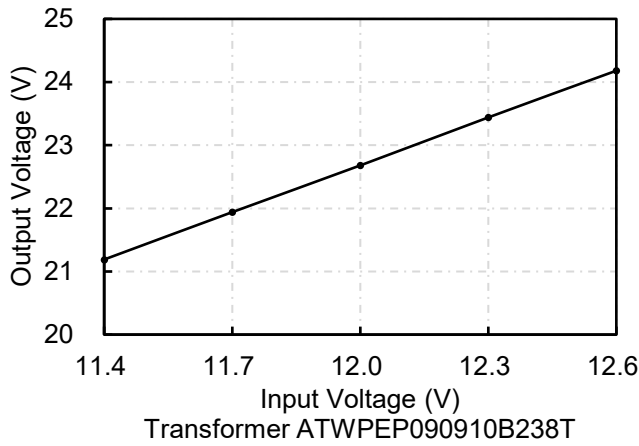


Figure 8.3 Output Voltage vs Input Voltage

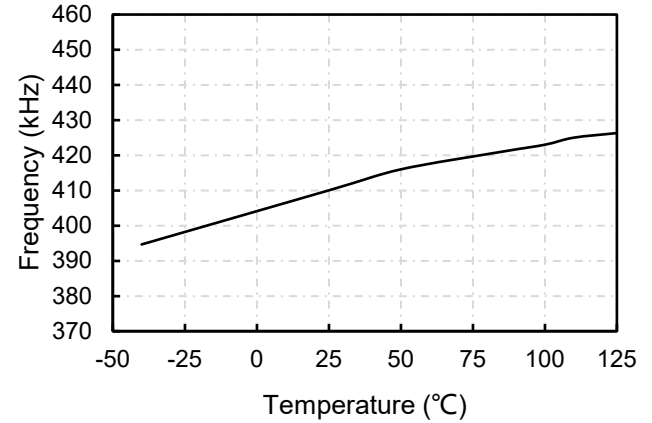


Figure 8.4 Frequency vs Free-Air Temperature at RT = 39.2kΩ

9. Parameter Measurement Information

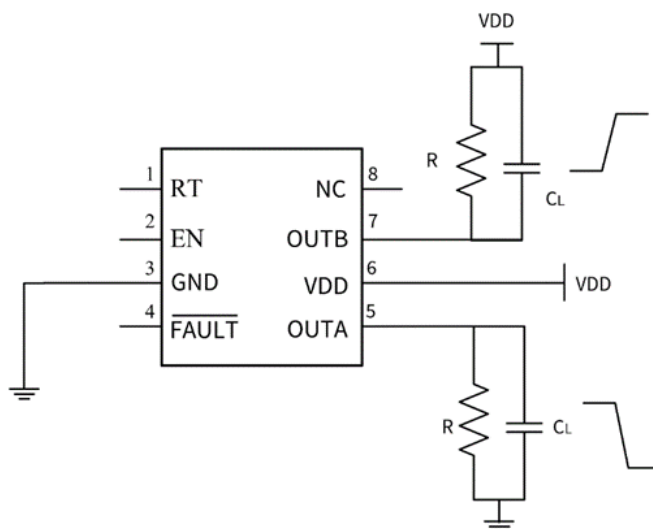


Figure 9.1 Test Circuit for T_R , T_F

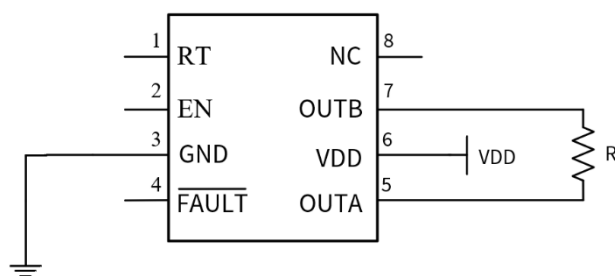


Figure 9.2 Test Circuit for DT

10. Function Description

10.1 Overview

The NSIP3266E is an isolated DC-DC switching controller optimized for H-bridge topologies. Compared to alternative solutions, the H-bridge architecture inherently simplifies design by eliminating the need for center-tapped transformers, reducing peripheral components, and lowering system cost. Operating from a wide input range of 6.5V to 26V, the device ensures broad compatibility across applications.

The NSIP3266E incorporates an overcurrent protection function that is triggered when the current exceeds safe thresholds, confining operation within the safe operating area (SOA) and shielding external components from surge damage. Switching frequency (100kHz–1MHz) is set via an external resistor on the RT pin for flexibility in efficiency and component size trade-offs.

The NSIP3266E provides a fault alarm signal (FAULT pin). When the device enters a short-circuit or overtemperature state, the FAULT pin outputs a low-level signal. If this pin is used, it should be connected to a 5V or 3.3V supply through a 10kΩ pull-up resistor. Additionally, the device includes internal oscillator and soft-start functions to eliminate dependency on external MCUs.

Functional Diagram

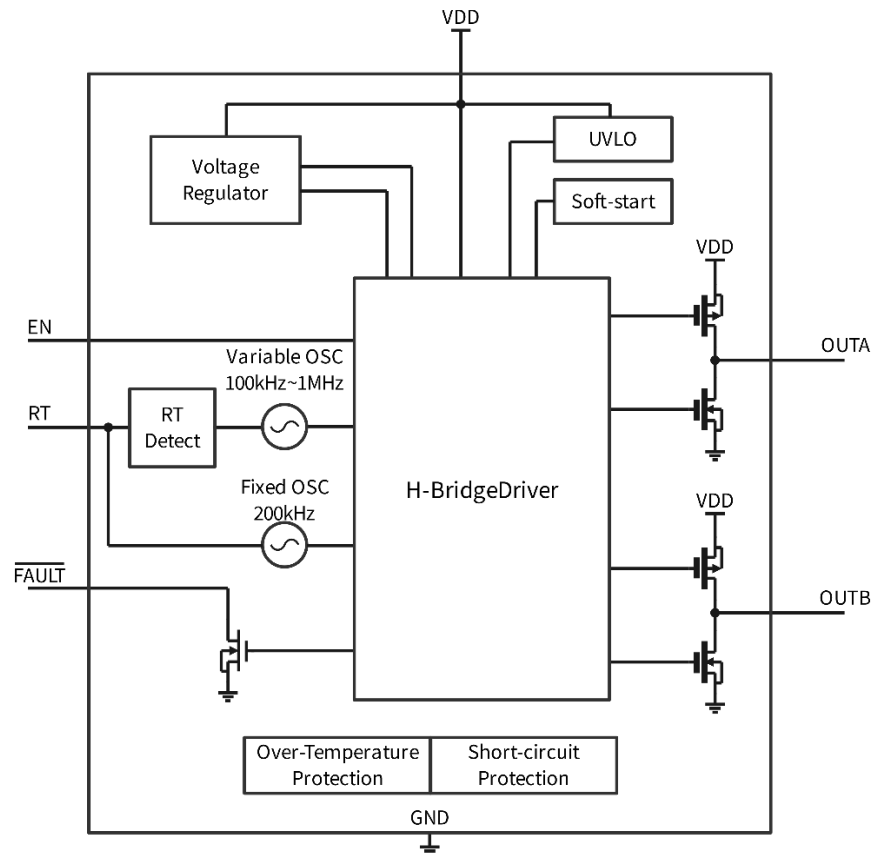


Figure 10.1 Functional Diagram

10.2 Feature Description

Start-Up Mode

Once the V_{DD} supply reaches 4.7V (typ) and the EN pin voltage rises above 2.1V (typ), the internal oscillator initiates operation, triggering switching activity in the output stage. However, during this initial phase, the gate voltage amplitude of MOSFETs D1 and D2 remains below its maximum rated value due to controlled soft-start behavior.

Soft Start

The NSIP3266E device implements a soft-start mechanism to prevent inrush current and protect transformers during startup. This feature is triggered under three conditions: initial power-up, enable signal (EN) rising edge, or post-protection recovery. During the soft-start period, the saturation current of the internal MOSFET is clamped at $I_{limit} = 550$ mA (typically), maintaining this regulated state for a fixed duration of $TSS_{max} = 40$ ms. Subsequently, the MOSFET enters a fully turned-on mode to minimize $R_{ds(on)}$, thereby reducing conduction losses. This design effectively balances smooth system startup, transformer protection, and power efficiency optimization, making it particularly suited for high-reliability power systems. The output

voltage (V_{out}) stabilization period (SST), influenced by load impedance and output capacitance, achieves a nominal value of <5ms under recommended operating conditions. The 40ms soft-start timing profile supports capacitive loads up to millifarad (mF) magnitudes, ensuring compatibility with high-energy storage applications.

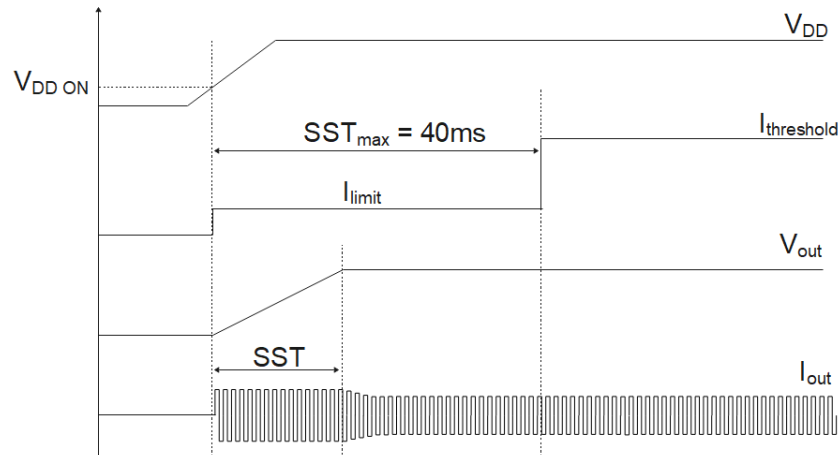


Figure 10.2 Waveform schematic diagram during soft start time

Disable Mode

The NSIP3266E incorporates a low-power disabled mode designed to minimize quiescent current consumption. When disabled, both OUTA and OUTB outputs enter a high-impedance (Hi-Z) state, effectively isolating the output stage to prevent unintended load interaction.

It should be noted that during the power-up sequence, if the VCC voltage exceeds 4.7V (typ) but remains below 6V (typ) while the EN voltage is above the lower threshold of 1.3V, the device will be in the enabled state.

Short-Circuit Protection and FAULT Asserts

The NSIP3266E features a multi-stage overcurrent protection (OCP) mechanism designed to address output overcurrent or short-circuit conditions. When the NMOS current exceeds a 2.6A (typical) threshold for 500ns, the protection system is triggered. Upon detection, the $\overline{\text{FAULT}}$ pin is immediately pulled low to disable N/PMOS switching signals, halting power delivery. If the fault persists, the system enters a 290ms hiccup shutdown phase to prevent thermal stress and component damage. After this period, the $\overline{\text{FAULT}}$ pin releases high, initiating a 40ms soft-start process to attempt system recovery. If the fault remains unresolved, the cycle (500ns detection, 290ms shutdown, and soft-start) repeats until normal operation resumes.

This hierarchical design ensures rapid fault response while prioritizing system safety. The 500ns deglitch time minimizes false triggers, and the hiccup mode reduces heat accumulation during prolonged faults. The inclusion of soft-start during recovery enables controlled power ramp-up, enhancing reliability in demanding applications. By balancing precision thresholds, thermal management, and staged recovery, the NSIP3266E delivers robust protection for power systems requiring high resilience.

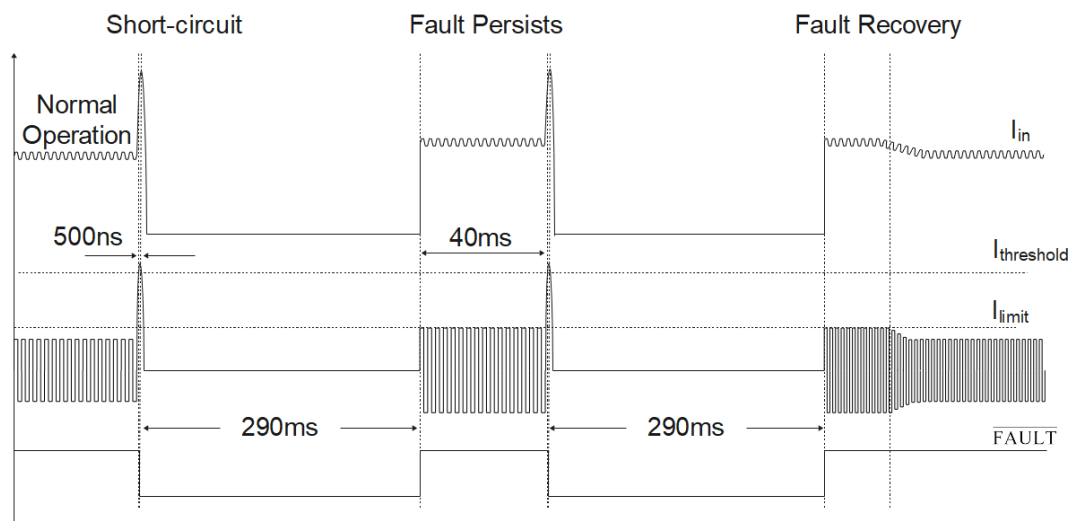


Figure 10.3 Waveform schematic diagram during over current protection

Over Temperature Protection

The NSIP3266E device supports overtemperature protection. When the junction temperature of the device is exceeds T_{SD+} , the device will turn off output to protect the device from overheating damage. When the junction temperature is lower than T_{SD-} , the device will resume startup.

Programming the Switching Frequency

The switching frequency f_{sw} of the NSIP3266E can be programmed by the resistor R_{set} connected between the RT pin and GND. The R_{set} can be determined by a given switching frequency. RT floating defaults to 200 kHz. Use Equation 1 or the curve in Figure 10.4.

$$R_{set} (k\Omega) = 28860 * f_{sw}(KHz)^{-1.104} \quad (1)$$

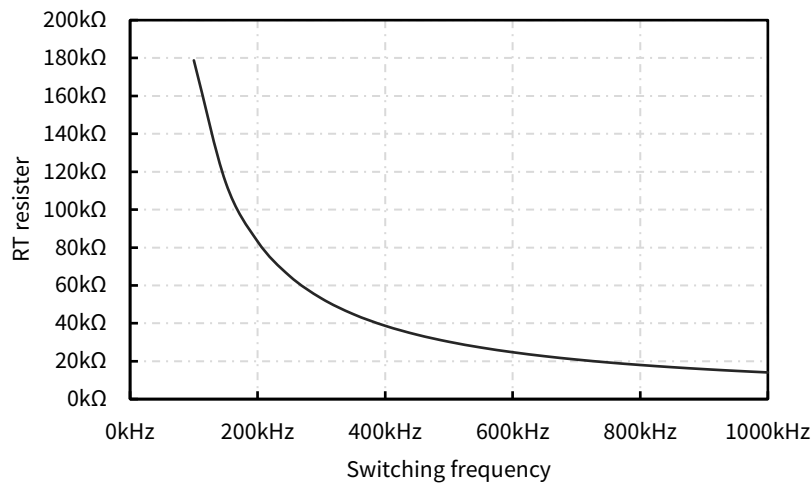


Figure 10.4 RT resistor vs Switching frequency

Table 10.1 gives typical R_{set} values for a given f_{sw} .

Table 10.1 Typical Frequency vs. RT Resistance

$R_{set} (k\Omega)$	$f_{sw}(kHz)$
180	100
68	246
33	464
24	607
20	700
16	900
13	1000

11. Application Note

11.1 Typical Application

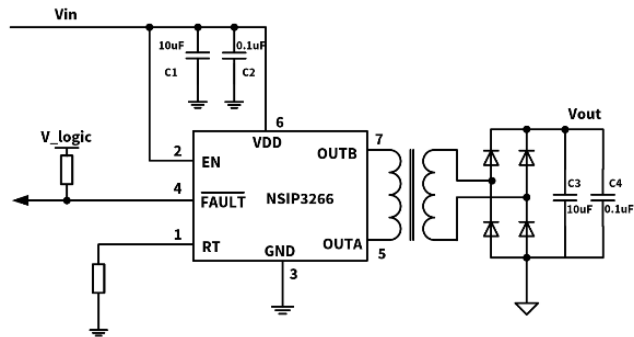


Figure 11.1 Typical Application Schematic

11.2 Design Requirements

For this design example, refer to Table 11.1 for key design parameters.

Table 11.1 Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	12 V $\pm$ 5%
Output voltage at full load	23 V
Maximum load current	170mA
Switching frequency	417KHz

11.2.1 Detailed Design Requirements

The following sections focus on the design of efficient H-bridge conversions with high voltage drive capability.

11.2.1.1 Input Capacitance Selection

As shown in Figure 11.1, capacitor C1 serves critical roles in input voltage stabilization, including energy buffering, low-frequency filtering, and bulk decoupling. To enhance high-frequency performance, ceramic capacitor C2 is deployed as a localized decoupling component and must be positioned in close proximity to the chip's power pins. During H-bridge converter switching transitions, C1 compensates for instantaneous current demands, with its capacitance value optimally selected between 1µF and 10µF. This range effectively balances transient response capability with input ripple attenuation, while C2 addresses high-frequency impedance through its ultra-low ESL characteristics. The dual-capacitor architecture ensures robust power integrity across both low and high frequency domains.

Voltage ratings must incorporate substantial derating margins (typically $\geq 150\%$ of maximum input voltage) to ensure reliable operation. Multilayer ceramic capacitors (MLCCs) are strongly recommended due to their ultra-low equivalent series resistance (ESR), minimal parasitic inductance, and stable X7R/X8R temperature characteristics.

11.2.1.2 Output Capacitance Selection

While the H-bridge converter theoretically supports 100% duty cycle operation for full energy transfer, practical implementation mandates a defined dead-time interval during complementary switching transitions. This prevents catastrophic shoot-through currents arising from simultaneous conduction in the bridge arms. During the dead-time phase, the output filter capacitor C3 assumes critical responsibility for maintaining load current continuity and voltage stability.

For optimal performance, C3 should be implemented as a multilayer ceramic capacitor (MLCC) with Capacitance range of 4.7µF to 10µF, which provides optimal filtering performance for the converter.

11.2.1.3 Output Rectifier Diode Selection

The selection of output rectifier diodes needs to consider the following four points:

- **Low Forward Voltage:** Prioritize diodes with low V_f (typically $< 0.4V$ at rated current) to minimize conduction losses and improve power supply efficiency.
- **Fast Recovery Speed:** Select diodes with short reverse recovery time (t_{rr}) to reduce switching losses and prevent voltage overshoot.
- **High Thermal Stability:** Choose diodes with stable forward voltage across temperature ranges, especially in high ambient temperatures (e.g., $> 85^{\circ}C$).

- **Minimal junction capacitance:** Considering the increase in output voltage caused by the oscillation of rectifier diode junction capacitance and transformer leakage inductance under light load, it is recommended to choose rectifier diodes with smaller junction capacitance as much as possible.

11.2.1.4 Transformer Selection

11.2.1.4.1 V-t Product Calculation

Transformer selection needs to consider the V_t factor. The purpose is to prevent transformer saturation. The $V_{t_{min}}$ is calculated by the maximum input voltage multiplying 50% of the maximum cycle time.

$$V_{t_{min}} \geq V_{IN-max} \times \frac{T_{max}}{2} = \frac{V_{IN-max}}{2 \times f_{min}} \quad (1)$$

Taking an example of f_{min} as 360kHz for NSIP3266, Equation 2 yields the minimum V-t products of:

$$V_{t_{min}} \geq \frac{12V \times 105\%}{2 \times 370kHz} = 17 V\mu s \quad \text{for } 12V \quad (2)$$

Other important factors such as isolation voltage, transformer power and turns ratio must be considered before the final selection decision is made.

11.2.1.4.2 Turns Ratio Estimate

Assuming the rectifier diode have been selected, the V-t product of the selected transformer is not less than 17.5V μ s. The minimum turns ratio that allows the H-bridge converter to operate perfectly over a specified current and temperature range needs to be determined.

The forward voltage drop V_F of the rectifier diode at maximum output load is to be considered.

$$V_{S-min} = V_{F-max} + V_{O-max} \quad (3)$$

The minimum available primary voltage V_{P-min} is calculated. Drain-source voltage of the NSIP3266E is V_{DS-max} . The minimum converter input voltage is V_{IN-min} :

$$V_{P-min} = V_{IN-min} - V_{DS-max} \quad (4)$$

V_{DS-max} is the product of the maximum $R_{DS(on)}$ and I_D values for a given supply specified in the NSIP3266E data sheet:

$$V_{DS-max} = (R_{OH-max} + R_{OL-max}) \times I_{Dmax} \quad (5)$$

Then inserting Equation 5 into Equation 4 yields:

$$V_{P-min} = V_{IN-min} - (R_{OH-max} + R_{OL-max}) \times I_{Dmax} \quad (6)$$

Inserting Equation 6 and Equation 3 into Equation 7 provides the minimum turns ratio:

$$N_{sp-min} = \frac{V_{F-max} + V_{O-max}}{V_{IN-min} - \frac{P_{O-max}}{\eta \times V_{IN-min}} \times (R_{OH-max} + R_{OL-max})} \quad (7)$$

Example:

For a 12 V_{IN} to 23 V_{OUT} converter using the rectifier diode MBRS140T3G, at a load current of 170 mA and a maximum temperature of 125°C, $V_{F-max} = 0.19V$, $V_{O_FullLoad_max} = 23 V$, and $I_{OUT-max} = 0.17A$.

Assume that the input power supply accuracy is $\pm 5\%$, $V_{IN-min} = 11.4 V$. From the NSIP3266E data sheet with $R_{OH-max} = 2.0\Omega$,

$R_{OL-max} = 1.5\Omega$, $I_{D-max} = 0.17A$.

Inserting these values and performing calculations:

$$N_{sp-min} = \frac{0.19V + 23V}{12V - \frac{23V \times 0.17A}{0.85 \times 11.4} \times (2.0 + 1.5)\Omega} = 2.2 \quad (8)$$

11.3 Layout

- A 1 μ F to 10 μ F low-ESR ceramic bypass capacitor should be connected between the VDD pin and ground to ensure stable power supply operation. The capacitor should be placed as close as possible to the VDD pin to minimize high-frequency impedance.
- The PCB layout is shown in Figure 11.2. The GND pin must be connected to the PCB ground plane via two vias to minimize inductance.
- The OUTA and OUTB pins of the device should be connected with the primary terminal of the transformer. The wiring connections must be as close together as possible to reduce the inductance of the wires.
- The recommended rectifier diode is the Schottky diode, which has a low forward voltage to maximize efficiency. However, if stringent output voltage regulation is required under light loads, please replace Schottky diodes with fast recovery diodes with smaller junction capacitance to achieve stable output voltage under light load.
- The V_{OUT} pins must be decoupled to the ISO ground with low-ESR ceramic bypass capacitors. A 10 μ F capacitor should be used in parallel with a 0.1 μ F capacitor, and the rated voltage of both capacitors is at least 35V.

Layout Example

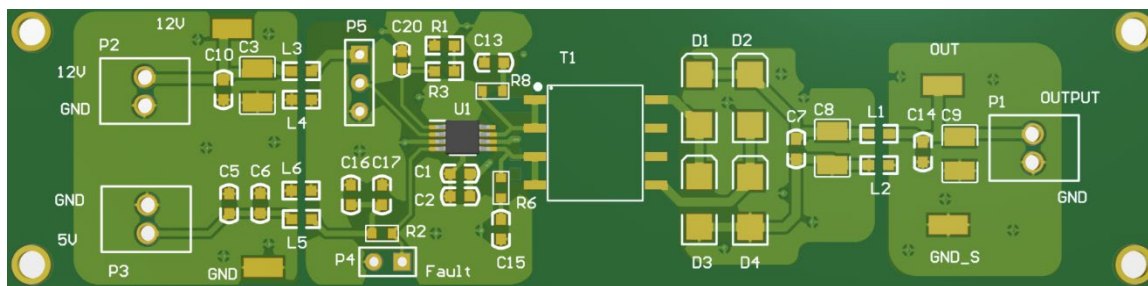
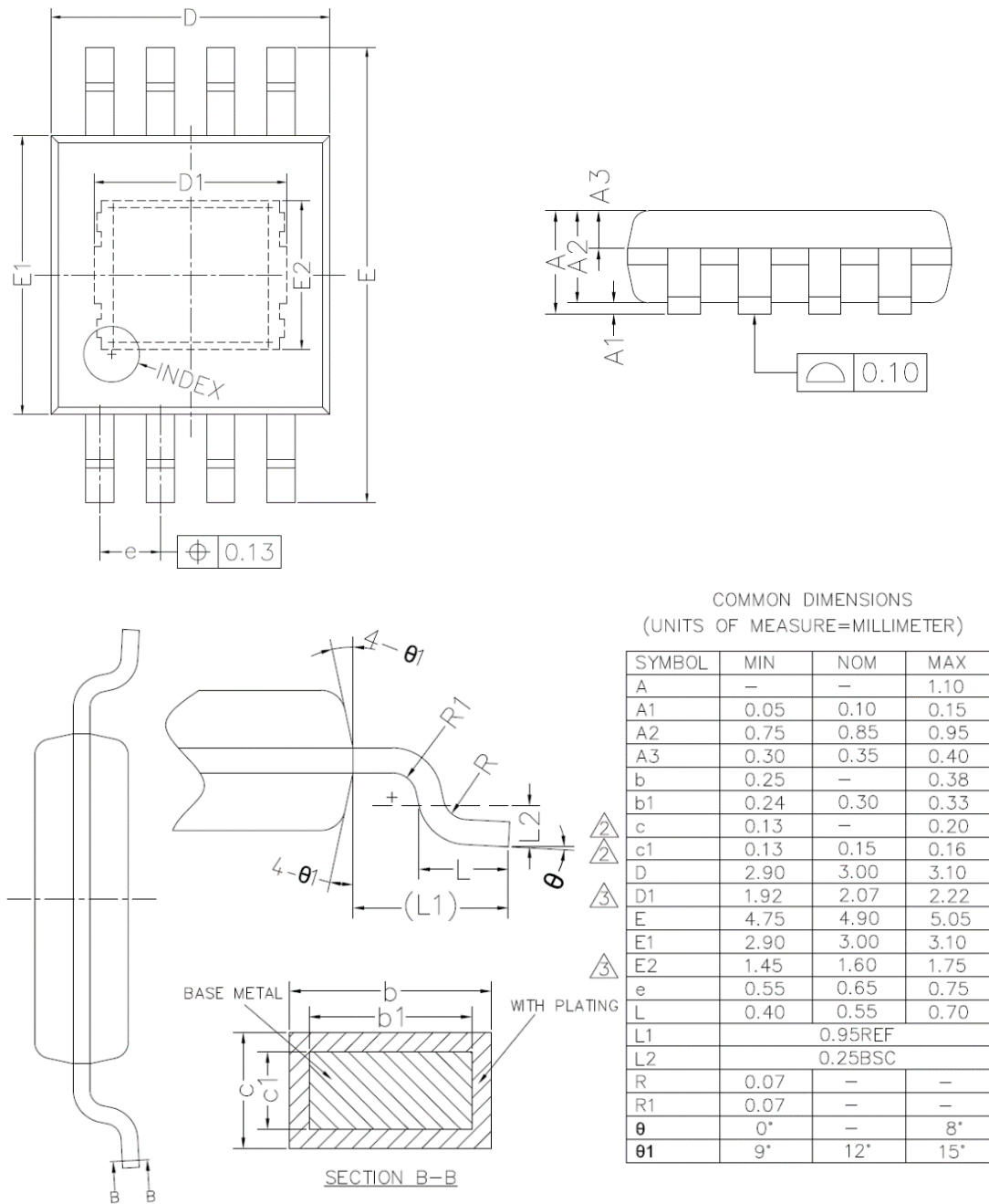


Figure 11.2 Layout Example of 2-Layer Board (NSIP3266E)

12. Package Information



- NOTES: 1. ALL DIMENSIONS IN MILLIMETERS REFER TO JEDEC STANDARD MO-187 AA-T DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.
2. INDEX $\phi 0.60 \pm 0.10$ WITH 0.05MAX DEPTH.
3. 'D1' AND 'E2' ARE VARIABLES DEPENDING ON DIE PAD SIZES.

Figure 12.1 HMSOP8 Package Shape and Dimension

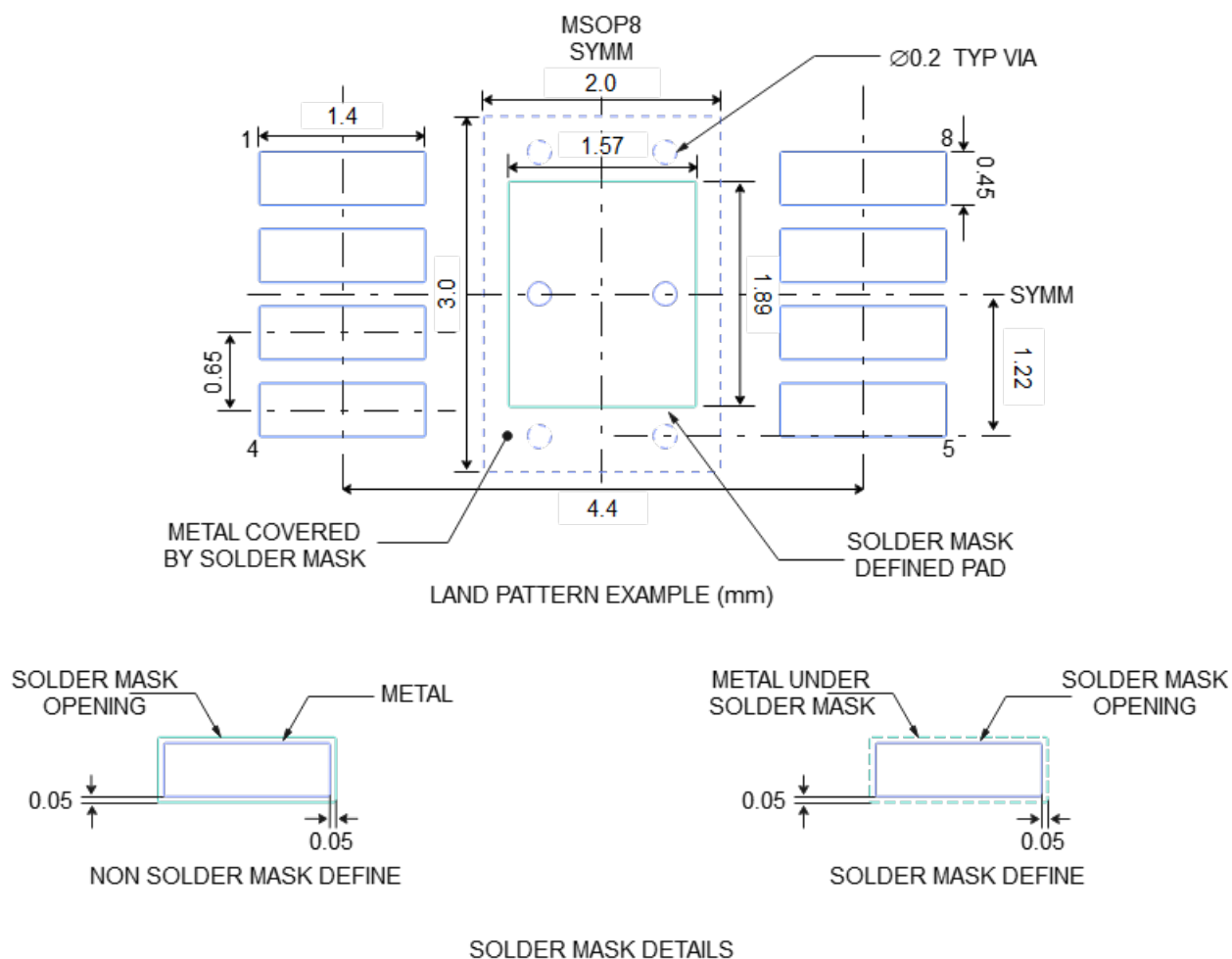


Figure 12.2 HMSOP8 Package Board Layout Example

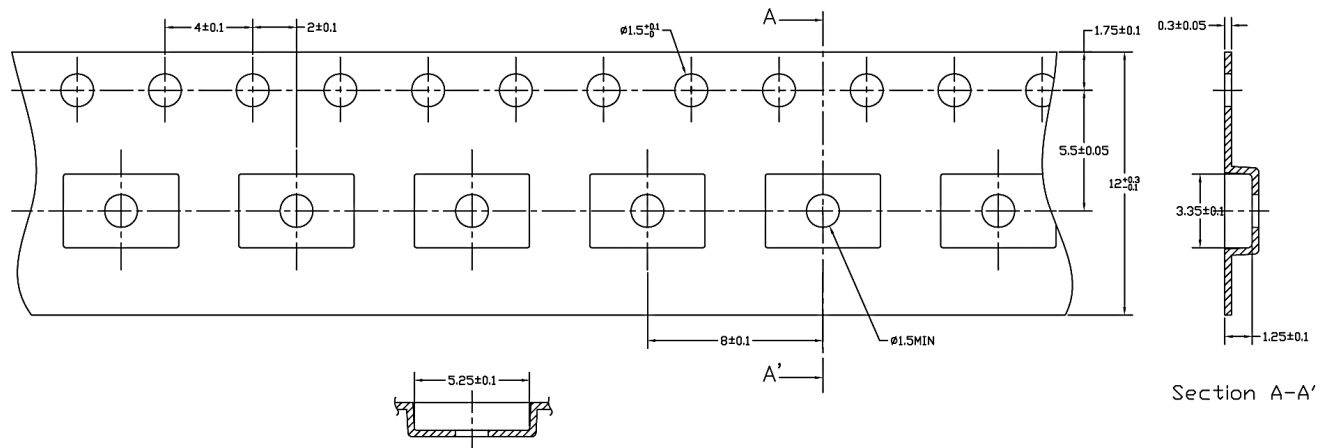
13. Ordering Information

Part No.	Temperature	Auto-motive	Package Drawing	MSL	SPQ
NSIP3266E-DHMSR	-40 to 125°C	N	HMSOP8	2	2500

14. Documentation Support

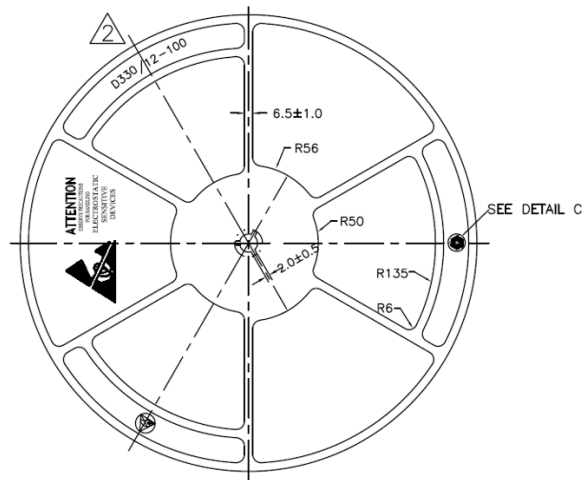
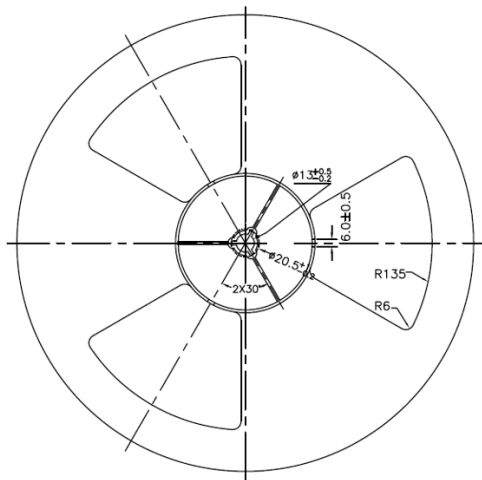
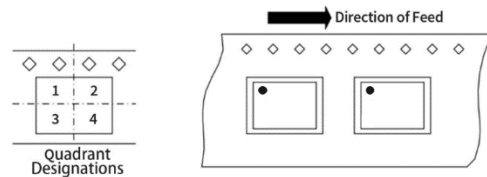
Part Number	Product Folder	Datasheet	Application Note
NSIP3266E-DHMSR	Click here	Click here	Click here

15. Tape and Reel Information



NOTES:

- 1.MATERIAL:Hard polystyrene(PS)
- 2.ALL DIMS IN MM
- 3.There must not be foreign body adhesion and the state of the surface must be excellent
- 4.The meander of the tape is assumed with 1mm or less every 100mm between 250mm
- 5.A permissible difference of the accumulation pitch of the sending hole is assumed to be ± 0.3 up to 50 pitches
- 6.Ø560 Paper-Reel, 60000 pockets(480M)
- 7.Corner R=0.3max
- 8.Surface resistance $1 \times 10^5 \leq R_s \leq 1 \times 10^9$ OHMS/SQ



NOTES:

- 1、Material: Polystyrene (black).
- 2、Flatness: Maximum allowed 3mm.
- 3、All dimensions are in millimeters.
- 4、Surface resistivity: 1×10^5 to 1×10^{10} OHMS/SQ.
- 5、All unmarked tolerances: ± 0.25 .

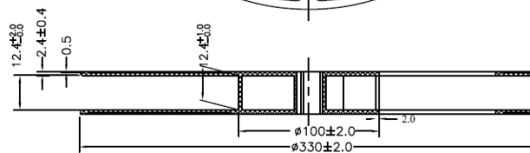


Figure 15.1 Tape and Reel Information of HMSOP8

16. Doc History

<i>Revision</i>	<i>Description</i>	<i>Date</i>
1.0	Initial Version	2026/05/02

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